

# Dual 4-Input Multiplexer with 3-State Outputs

## MC74AC253, MC74ACT253

The MC74AC253/74ACT253 is a dual 4-input multiplexer with 3-state outputs. It can select two bits of data from four sources using common select inputs. The outputs may be individually switched to a high impedance state with a HIGH on the respective Output Enable  $(\overline{OE})$  inputs, allowing the outputs to interface directly with bus oriented systems.

- Multifunctional Capability
- Noninverting 3–State Outputs
- Outputs Source/Sink 24 mA
- 'ACT253 Has TTL Compatible Inputs
- These are Pb-Free Devices

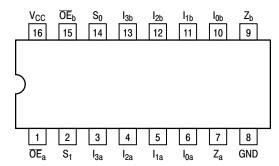


Figure 1. Pinout: 16-Lead Packages Conductors (Top View)

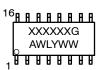
## **PIN NAME**

PIN	FUNCTION
I <sub>0a</sub> -I <sub>3a</sub>	Side A Data Inputs
I <sub>0b</sub> -I <sub>3b</sub>	Side B Data Inputs
S <sub>0</sub> , S <sub>1</sub>	Common Select Inputs
ŌΕ <sub>a</sub>	Side A Output Enable Input
ŌE <sub>b</sub>	Side B Output Enable Input
$Z_{a,}Z_{b}$	3-State Outputs

## MARKING DIAGRAMS



SOIC-16 D SUFFIX CASE 751B



XXX = Specific Device Code A = Assembly Location

WL = Wafer Lot
 Y = Year
 WW = Work Week
 G = Pb-Free Package

(Note: Microdot may be in either location)

## ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 7 of this data sheet.

## **TRUTH TABLE**

Select Inputs			Data I	nputs	Output Enable	Outputs	
S <sub>0</sub>	S <sub>1</sub>	I <sub>0</sub>	l <sub>1</sub>	l <sub>2</sub>	l <sub>3</sub>	ŌĒ	Z
Х	Χ	Χ	Χ	Χ	Χ	Н	Z
L	L	L	X	X	X	L	L
L	L	Н	X	X	Х	L	Н
Н	L	X	L	X	X	L	L
Н	L	X	Н	X	X	L	Н
L	Н	Х	Х	L	Х	L	L
L	Н	X	X	Н	X	L	Н
Н	Н	X	X	X	L	L	L
Н	Н	Χ	Χ	Х	Н	L	Н

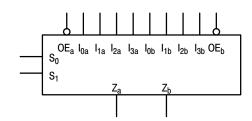


Figure 2. Logic Symbol

Address inputs  $S_0$  and  $S_1$  are common to both sections.

H = HIGH Voltage Level

L = LOW Voltage Level

X = Immaterial

Z = High Impedance

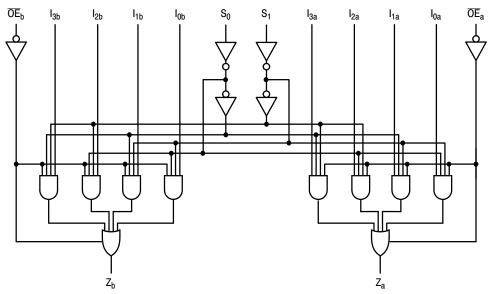
## **FUNCTIONAL DESCRIPTION**

The MC74AC253/74ACT253 contains two identical 4–input multiplexers with 3–state outputs. They select two bits from four sources selected by common Select inputs ( $S_0$ ,  $S_1$ ). The 4–input multiplexers have individual Output Enable ( $\overline{OE}_a$ ,  $\overline{OE}_b$ ) inputs which, when HIGH, force the outputs to a high impedance (High Z) state. This device is the logic implementation of a 2–pole, 4–position switch, where the position of the switch is determined by the logic levels

supplied to the two select inputs. The logic equations for the outputs are shown:

$$\begin{split} Z_{a} &= \overline{OE}_{a} \bullet (I_{0a} \bullet \overline{S}_{1} \bullet \overline{S}_{0} + I_{1a} \bullet \overline{S}_{1} \bullet S_{0} + I_{2a} \bullet S_{1} \bullet S_{0}) \\ I_{2a} \bullet S_{1} \bullet \overline{S}_{0} + I_{3a} \bullet S_{1} \bullet S_{0}) \\ Z_{b} &= \overline{OE}_{b} \bullet (I_{0b} \bullet \overline{S}_{1} \bullet \overline{S}_{0} + I_{1b} \bullet \overline{S}_{1} \bullet S_{0} + I_{2b} \bullet S_{1} \bullet \overline{S}_{0} + I_{3b} \bullet S_{1} \bullet S_{0}) \end{split}$$

If the outputs of 3-state devices are tied together, all but one device must be in the high impedance state to avoid high currents that would exceed the maximum ratings. Designers should ensure that Output Enable signals to 3-state devices whose outputs are tied together are designed so that there is no overlap.



NOTE: This diagram is provided only for the understanding of logic operations and should not be used to estimate propagation delays.

Figure 3. Logic Diagram

## **MAXIMUM RATINGS**

Symbol	Parameter		Value	Unit
V <sub>CC</sub>	DC Supply Voltage		-0.5 to +6.5	V
VI	DC Input Voltage		$-0.5 \le V_{CC} + 0.5$	V
Vo	DC Output Voltage (Note 1)		$-0.5 \le V_{CC} + 0.5$	V
I <sub>IK</sub>	DC Input Diode Current		±20	mA
I <sub>OK</sub>	DC Output Diode Current		±50	mA
I <sub>O</sub>	DC Output Sink/Source Current		±50	mA
I <sub>CC</sub>	DC Supply Current per Output Pin		±50	mA
I <sub>GND</sub>	DC Ground Current per Output Pin	±50		mA
T <sub>STG</sub>	Storage Temperature Range		-65 to +150	°C
TL	Lead temperature, 1 mm from Case for 10 Seconds		260	°C
TJ	Junction temperature under Bias		+150	°C
$\theta_{JA}$	Thermal Resistance (Note 2)	SOIC	126	°C/W
P <sub>D</sub>	Power Dissipation in Still Air at 25°C (Note 3)	SOIC	995	mW
MSL	Moisture Sensitivity		Level 1	
F <sub>R</sub>	Flammability Rating Oxygen In	dex: 30% - 35%	UL 94 V-0 @ 0.125 in	
V <sub>ESD</sub>		y Model (Note 4) e Model (Note 5)	> 2000 > 1000	V
I <sub>Latch-Up</sub>	Latch-Up Performance Above V <sub>CC</sub> and Below GND	at 85°C (Note 6)	±100	mA

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

- 1. I<sub>O</sub> absolute maximum rating must be observed.
- 2. The package thermal impedance is calculated in accordance with JESD51-7.
- 3. 500 mW at 65°C; derate to 300 mW by 10 mW/ from 65°C to 85°C.
- 4. Tested to EIA/JESD22-A114-A.
- 5. Tested to JESD22-C101-A.
- 6. Tested to EIA/JESD78.

## RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Min	Тур	Max	Unit	
V	Consulta Valta and	'AC	2.0	5.0	6.0	V
V <sub>CC</sub>	Supply Voltage	'ACT	4.5	5.0	5.5	V
V <sub>IN</sub> , V <sub>OUT</sub>	DC Input Voltage, Output Voltage (Ref. to GND)		0	-	V <sub>CC</sub>	V
		V <sub>CC</sub> @ 3.0 V	-	150	-	
t <sub>r</sub> , t <sub>f</sub>	Input Rise and Fall Time (Note 1)  'AC Devices except Schmitt Inputs	V <sub>CC</sub> @ 4.5 V	-	40	-	ns/V
	// C Devices except commit impate	V <sub>CC</sub> @ 5.5 V	-	25	-	
	Input Rise and Fall Time (Note 2)	V <sub>CC</sub> @ 4.5 V	-	10	-	no //
t <sub>r</sub> , t <sub>f</sub>	'ACT Devices except Schmitt Inputs V <sub>CC</sub> @ 5.5 V		-	8.0	_	ns/V
T <sub>A</sub>	Operating Ambient Temperature Range		-40	25	85	°C
I <sub>OH</sub>	Output Current - High		-	-	-24	mA
I <sub>OL</sub>	Output Current – Low		-	-	24	mA

Functional operation above the stresses listed in the Recommended Operating Ranges is not implied. Extended exposure to stresses beyond the Recommended Operating Ranges limits may affect device reliability.

- V<sub>IN</sub> from 30% to 70% V<sub>CC</sub>; see individual Data Sheets for devices that differ from the typical input rise and fall times.
   V<sub>IN</sub> from 0.8 V to 2.0 V; see individual Data Sheets for devices that differ from the typical input rise and fall times.

## **DC CHARACTERISTICS**

	Parameter		74	AC	74AC		
Symbol		V <sub>CC</sub> (V)	T <sub>A</sub> = +25°C		T <sub>A</sub> = -40°C to +85°C	Unit	Conditions
			Тур	Guar	anteed Limits		
V <sub>IH</sub>	Minimum High Level Input Voltage	3.0 4.5 5.5	1.5 2.25 2.75	2.1 3.15 3.85	2.1 3.15 3.85	V	V <sub>OUT</sub> = 0.1 V or V <sub>CC</sub> – 0.1 V
V <sub>IL</sub>	Maximum Low Level Input Voltage	3.0 4.5 5.5	1.5 2.25 2.75	0.9 1.35 1.65	0.9 1.35 1.65	V	V <sub>OUT</sub> = 0.1 V or V <sub>CC</sub> – 0.1 V
V <sub>OH</sub>	Minimum High Level Output Voltage	3.0 4.5 5.5	2.99 4.49 5.49	2.9 4.4 5.4	2.9 4.4 5.4	٧	I <sub>OUT</sub> = -50 μA
		3.0 4.5 5.5	- - -	2.56 3.86 4.86	2.46 3.76 4.76	V	$*V_{IN} = V_{IL} \text{ or } V_{IH}$ $-12 \text{ mA}$ $I_{OH}$ $-24 \text{ mA}$ $-24 \text{ mA}$
V <sub>OL</sub>	Maximum Low Level Output Voltage	3.0 4.5 5.5	0.002 0.001 0.001	0.1 0.1 0.1	0.1 0.1 0.1	V	Ι <sub>ΟUT</sub> = 50 μΑ
		3.0 4.5 5.5	- - -	0.36 0.36 0.36	0.44 0.44 0.44	V	*V <sub>IN</sub> = V <sub>IL</sub> or V <sub>IH</sub> 12 mA I <sub>OL</sub> 24 mA 24 mA
I <sub>IN</sub>	Maximum Input Leakage Current	5.5	-	±0.1	±1.0	μΑ	$V_I = V_{CC}$ , GND
I <sub>OZ</sub>	Maximum 3-State Current	5.5	-	±0.5	±5.0	μΑ	$\begin{aligned} &V_{I}\left(OE\right)=V_{IL},V_{IH}\\ &V_{I}=V_{CC},GND\\ &V_{O}=V_{CC},GND \end{aligned}$
I <sub>OLD</sub>	†Minimum Dynamic	5.5	-	-	75	mA	V <sub>OLD</sub> = 1.65 V Max
I <sub>OHD</sub>	Output Current	5.5	-	_	-75	mA	V <sub>OHD</sub> = 3.85 V Min
Icc	Maximum Quiescent Supply Current	5.5	-	8.0	80	μΑ	V <sub>IN</sub> = V <sub>CC</sub> or GND

<sup>\*</sup>All outputs loaded; thresholds on input associated with output under test. †Maximum test duration 2.0 ms, one output loaded at a time.

NOTE: I<sub>IN</sub> and I<sub>CC</sub> @ 3.0 V are guaranteed to be less than or equal to the respective limit @ 5.5 V V<sub>CC</sub>.

## **AC CHARACTERISTICS**

				74AC		74	AC	
Symbol	Parameter	V <sub>CC</sub> * (V)				T <sub>A</sub> = - to +8 C <sub>L</sub> = 8	Unit	
			Min	Тур	Max	Min	Max	
t <sub>PLH</sub>	Propagation Delay S <sub>n</sub> to Z <sub>n</sub>	3.3 5.0	2.0 2.0	-	15.5 11.0	2.0 1.5	17.5 12.5	ns
t <sub>PHL</sub>	Propagation Delay S <sub>n</sub> to Z <sub>n</sub>	3.3 5.0	2.5 2.0	-	16.0 11.5	2.0 1.5	18.0 13.0	ns
t <sub>PLH</sub>	Propagation Delay $I_n$ to $Z_n$	3.3 5.0	1.5 1.5	-	14.5 10.0	1.5 1.5	17.0 11.5	ns
t <sub>PHL</sub>	Propagation Delay $I_n$ to $Z_n$	3.3 5.0	2.0 1.5	1 1	13.0 9.5	1.5 1.5	15.0 11.0	ns
t <sub>PZH</sub>	Output Enable Time	3.3 5.0	1.5 1.5	1 1	8.0 6.0	1.0 1.0	8.5 6.5	ns
t <sub>PZL</sub>	Output Enable Time	3.3 5.0	1.5 1.5	1 1	8.0 6.0	1.0 1.0	9.0 7.0	ns
t <sub>PHZ</sub>	Output Disable Time	3.3 5.0	2.0 2.0	1 1	9.5 8.0	1.5 1.5	10.0 8.5	ns
t <sub>PLZ</sub>	Output Disable Time	3.3 5.0	1.5 1.5	-	8.0 7.0	1.0 1.0	9.0 7.5	ns

<sup>\*</sup>Voltage Range 3.3 V is 3.3 V  $\pm$ 0.3 V. \*Voltage Range 5.0 V is 5.0 V  $\pm$ 0.5 V.

## **DC CHARACTERISTICS**

	Parameter		74	CT	74ACT		
Symbol		V <sub>CC</sub> (V)	T <sub>A</sub> = +25°C		T <sub>A</sub> = -40°C to +85°C	Unit	Conditions
			Тур	Guar	Guaranteed Limits		
V <sub>IH</sub>	Minimum High Level Input Voltage	4.5 5.5	1.5 1.5	2.0 2.0	2.0 2.0	V	V <sub>OUT</sub> = 0.1 V or V <sub>CC</sub> – 0.1 V
V <sub>IL</sub>	Maximum Low Level Input Voltage	4.5 5.5	1.5 1.5	0.8 0.8	0.8 0.8	V	V <sub>OUT</sub> = 0.1 V or V <sub>CC</sub> – 0.1 V
V <sub>OH</sub>	Minimum High Level Output Voltage	4.5 5.5	4.49 5.49	4.4 5.4	4.4 5.4	V	I <sub>OUT</sub> = -50 μA
		4.5 5.5	- -	3.86 4.86	3.76 4.76	٧	$*V_{IN} = V_{IL} \text{ or } V_{IH}$ $-24 \text{ mA}$ $I_{OH}$ $-24 \text{ mA}$
V <sub>OL</sub>	Maximum Low Level Output Voltage	4.5 5.5	0.001 0.001	0.1 0.1	0.1 0.1	V	I <sub>OUT</sub> = 50 μA
		4.5 5.5	- -	0.36 0.36	0.44 0.44	V	$*V_{IN} = V_{IL} \text{ or } V_{IH}$ $^{24} \text{ mA}$ $^{I}_{OL} \qquad ^{24} \text{ mA}$
I <sub>IN</sub>	Maximum Input Leakage Current	5.5	-	±0.1	±1.0	μΑ	V <sub>I</sub> = V <sub>CC</sub> , GND
$\Delta I_{CCT}$	Additional Max. I <sub>CC</sub> /Input	5.5	0.6	-	1.5	mA	$V_{I} = V_{CC} - 2.1 \text{ V}$
l <sub>OZ</sub>	Maximum 3-State Current	5.5	_	±0.5	±5.0	μА	$V_{I}$ (OE) = $V_{IL}$ , $V_{IH}$ $V_{I}$ = $V_{CC}$ , GND $V_{O}$ = $V_{CC}$ , GND
I <sub>OLD</sub>	†Minimum Dynamic	5.5	-	-	75	mA	V <sub>OLD</sub> = 1.65 V Max
I <sub>OHD</sub>	Output Current	5.5	-	_	-75	mA	V <sub>OHD</sub> = 3.85 V Min
I <sub>CC</sub>	Maximum Quiescent Supply Current	5.5	-	8.0	80	μΑ	V <sub>IN</sub> = V <sub>CC</sub> or GND

<sup>\*</sup>All outputs loaded; thresholds on input associated with output under test.  $\dagger$ Maximum test duration 2.0 ms, one output loaded at a time.

## **AC CHARACTERISTICS**

				74ACT		74	CT	
		v <sub>cc</sub> *		<sub>A</sub> = +25° <sub>L</sub> = 50 p		to +8	-40°C 85°C 50 pF	
Symbol	Parameter	(V)	Min	Тур	Max	Min	Max	Unit
t <sub>PLH</sub>	Propagation Delay S <sub>n</sub> to Z <sub>n</sub>	5.0	2.0	-	11.5	2.0	13.0	ns
t <sub>PHL</sub>	Propagation Delay S <sub>n</sub> to Z <sub>n</sub>	5.0	3.0	-	13.0	2.5	14.5	ns
t <sub>PLH</sub>	Propagation Delay I <sub>n</sub> to Z <sub>n</sub>	5.0	2.5	-	10.0	2.0	11.0	ns
t <sub>PHL</sub>	Propagation Delay $I_n$ to $Z_n$	5.0	3.5	-	11.0	3.0	12.5	ns
t <sub>PZH</sub>	Output Enable Time	5.0	2.0	-	7.5	1.5	8.5	ns
t <sub>PZL</sub>	Output Enable Time	5.0	2.0	-	8.0	1.5	9.0	ns
t <sub>PHZ</sub>	Output Disable Time	5.0	2.0	-	9.5	2.0	10.0	ns
t <sub>PLZ</sub>	Output Disable Time	5.0	2.0	_	7.5	2.0	8.5	ns

<sup>\*</sup> Voltage Range 5.0 V is 5.0 V  $\pm 0.5$  V.

## **CAPACITANCE**

Symbol	Parameter	Value Typ	Unit	Test Conditions
C <sub>IN</sub>	Input Capacitance	4.5	pF	V <sub>CC</sub> = 5.0 V
C <sub>PD</sub>	Power Dissipation Capacitance	50	pF	V <sub>CC</sub> = 5.0 V

## **ORDERING INFORMATION**

Device Order Number	Marking	Package	Shipping <sup>†</sup>
MC74AC253DR2G	AC253	SOIC-16 (Pb-Free)	2500 Tape & Reel
MC74ACT253DR2G	ACT253	SOIC-16 (Pb-Free)	2500 Tape & Reel

<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

## **REVISION HISTORY**

Revision	Description of Changes	Date
9	Change three values in the AC characteristics table	5/20/2025



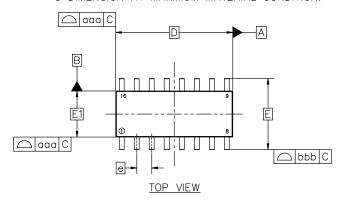


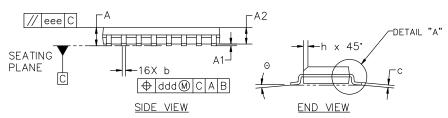
## SOIC-16 9.90x3.90x1.37 1.27P CASE 751B ISSUE M

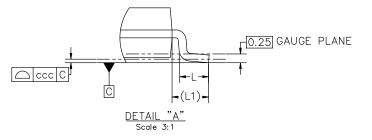
**DATE 18 OCT 2024** 

## NOTES:

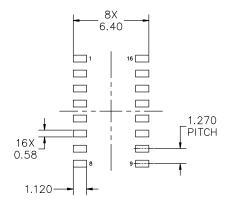
- 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2018.
- 2. DIMENSION IN MILLIMETERS. ANGLE IN DEGREES.
- 3. DIMENSIONS D AND E1 DO NOT INCLUDE MOLD PROTRUSION.
- 4. MAXIMUM MOLD PROTRUSION 0.15mm PER SIDE.
- 5. DIMENSION 6 DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.127mm TOTAL IN EXCESS OF THE 6 DIMENSION AT MAXIMUM MATERIAL CONDITION.







MILLIMETERS								
DIM	MIN	NOM	MAX					
А	1.35	1.55	1.75					
A1	0.10	0.18	0.25					
A2	1.25	1.37	1.50					
b	0.35	0.42	0.49					
С	0.19	0.22	0.25					
D		9.90 BSC						
Е	6.00 BSC							
E1		3.90 BSC						
е		1.27 BSC						
h	0.25		0.50					
L	0.40	0.83	1.25					
L1		1.05 REF						
Θ	0.		7.					
TOLERAN	CE OF FC	RM AND	POSITION					
aaa	0.10							
bbb	0.20							
ccc	0.10							
ddd	0.25							
eee		0.10						



## RECOMMENDED MOUNTING FOOTPRINT

\*FOR ADDITIONAL INFORMATION ON OUR PB-FREE STRATEGY AND SOLDERING DETAILS, PLEASE DOWNLOAD THE onsemi SOLDERING AND MOUNTING TECHNIQUES REFERENCE MANUAL, SOLDERRM/D

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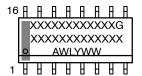
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## **SOIC-16 9.90x3.90x1.37 1.27P** CASE 751B

ISSUE M

**DATE 18 OCT 2024** 

# GENERIC MARKING DIAGRAM\*



XXXXX = Specific Device Code A = Assembly Location

WL = Wafer Lot
 Y = Year
 WW = Work Week
 G = Pb-Free Package

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

STYLE 1:		STYLE 2:		STYLE 3:	S	TYLE 4:	
	COLLECTOR	PIN 1.	CATHODE	PIN 1.	COLLECTOR, DYE #1	PIN 1.	COLLECTOR, DYE #1
	BASE	2.	ANODE	2.	BASE. #1	2.	
3.	EMITTER	3.	NO CONNECTION	3.	EMITTER. #1	3.	
4.	NO CONNECTION	4.	CATHODE	4.	COLLECTOR, #1	4.	COLLECTOR, #2
5.	EMITTER	5.	CATHODE	5.	COLLECTOR, #2	5.	COLLECTOR, #3
6.	BASE	6.	NO CONNECTION	6.	BASE, #2	6.	COLLECTOR, #3
7.	COLLECTOR	7.	ANODE	7.	EMITTER, #2	7.	COLLECTOR, #4
8.	COLLECTOR	8.	CATHODE	8.	COLLECTOR, #2	8.	COLLECTOR, #4
9.	BASE	9.	CATHODE	9.	COLLECTOR, #3	9.	BASE, #4
10.	EMITTER	10.	ANODE	10.	BASE, #3	10.	EMITTER, #4
11.	NO CONNECTION	11.	NO CONNECTION	11.	EMITTER, #3	11.	
	EMITTER	12.	CATHODE	12.		12.	
13.	BASE	13.		13.	COLLECTOR, #4	13.	BASE, #2
14.	COLLECTOR	14.	NO CONNECTION	14.	BASE, #4	14.	
15.	EMITTER	15.	ANODE	15.	EMITTER, #4	15.	
16.	COLLECTOR	16.	CATHODE	16.	COLLECTOR, #4	16.	EMITTER, #1
STYLE 5:		STYLE 6:		STYLE 7:			
PIN 1.	DRAIN, DYE #1	PIN 1.	CATHODE	PIN 1.	SOURCE N-CH		
2.	DRAIN, #1	2.	CATHODE	2.	COMMON DRAIN (OUTPUT)		
3.	DRAIN. #2				COMMON DOMINI (OLITOLIT)		
	שוויאווי, דב	3.	CATHODE	3.	COMMON DRAIN (OUTPUT)		
4.		3. 4.	CATHODE	3. 4.			
4. 5.	DRAIN, #2 DRAIN, #3		CATHODE CATHODE		GATE P-CH COMMON DRAIN (OUTPUT)		
5. 6.	DRAIN, #2 DRAIN, #3 DRAIN, #3	4. 5. 6.	CATHODE CATHODE CATHODE	4. 5. 6.	GATE P-CH COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT)		
5.	DRAIN, #2 DRAIN, #3 DRAIN, #3 DRAIN, #4	4. 5. 6. 7.	CATHODE CATHODE CATHODE CATHODE	4. 5. 6. 7.	GATE P-CH COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT)		
5. 6. 7. 8.	DRAIN, #2 DRAIN, #3 DRAIN, #3 DRAIN, #4 DRAIN, #4	4. 5. 6. 7.	CATHODE CATHODE CATHODE CATHODE CATHODE	4. 5. 6. 7. 8.	GATE P-CH COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT) SOURCE P-CH		
5. 6. 7. 8.	DRAIN, #2 DRAIN, #3 DRAIN, #3 DRAIN, #4 DRAIN, #4 GATE, #4	4. 5. 6. 7. 8.	CATHODE CATHODE CATHODE CATHODE CATHODE ANODE	4. 5. 6. 7. 8. 9.	GATE P-CH COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT) SOURCE P-CH SOURCE P-CH		
5. 6. 7. 8. 9.	DRAIN, #2 DRAIN, #3 DRAIN, #3 DRAIN, #4 DRAIN, #4 GATE, #4 SOURCE, #4	4. 5. 6. 7. 8. 9.	CATHODE CATHODE CATHODE CATHODE CATHODE ANODE ANODE	4. 5. 6. 7. 8. 9.	GATE P-CH COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT) SOURCE P-CH SOURCE P-CH COMMON DRAIN (OUTPUT)		
5. 6. 7. 8. 9. 10.	DRAIN, #2 DRAIN, #3 DRAIN, #3 DRAIN, #4 DRAIN, #4 GATE, #4 SOURCE, #4 GATE, #3	4. 5. 6. 7. 8. 9. 10.	CATHODE CATHODE CATHODE CATHODE CATHODE ANODE ANODE ANODE ANODE	4. 5. 6. 7. 8. 9. 10.	GATE P-CH COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT) SOURCE P-CH SOURCE P-CH COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT)		
5. 6. 7. 8. 9. 10. 11.	DRAIN, #2 DRAIN, #3 DRAIN, #3 DRAIN, #4 DRAIN, #4 GATE, #4 SOURCE, #4 GATE, #3 SOURCE, #3	4. 5. 6. 7. 8. 9. 10. 11.	CATHODE CATHODE CATHODE CATHODE CATHODE ANODE ANODE ANODE ANODE ANODE ANODE	4. 5. 6. 7. 8. 9. 10. 11.	GATE P-CH COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT) SOURCE P-CH SOURCE P-CH COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT)		
5. 6. 7. 8. 9. 10. 11. 12.	DRAIN, #2 DRAIN, #3 DRAIN, #3 DRAIN, #4 DRAIN, #4 GATE, #4 SOURCE, #4 GATE, #3 SOURCE, #3 GATE, #2	4. 5. 6. 7. 8. 9. 10. 11. 12.	CATHODE CATHODE CATHODE CATHODE CATHODE CATHODE ANODE ANODE ANODE ANODE ANODE ANODE ANODE	4. 5. 6. 7. 8. 9. 10. 11. 12.	GATE P-CH COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT) SOURCE P-CH SOURCE P-CH COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT) GATE N-CH		
5. 6. 7. 8. 9. 10. 11. 12. 13.	DRAIN, #2 DRAIN, #3 DRAIN, #3 DRAIN, #4 DRAIN, #4 GATE, #4 GATE, #4 GATE, #3 SOURCE, #3 GOURCE, #3 GOURCE, #2 SOURCE, #2	4. 5. 6. 7. 8. 9. 10. 11. 12. 13.	CATHODE CATHODE CATHODE CATHODE CATHODE CATHODE ANODE	4. 5. 6. 7. 8. 9. 10. 11. 12. 13.	GATE P-CH COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT) SOURCE P-CH SOURCE P-CH COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT) CATE N-CH COMMON DRAIN (OUTPUT)		
5. 6. 7. 8. 9. 10. 11. 12. 13. 14.	DRAIN, #2 DRAIN, #3 DRAIN, #3 DRAIN, #4 DRAIN, #4 SOURCE, #4 GATE, #3 SOURCE, #3 GATE, #2 SOURCE, #2 GATE, #1	4. 5. 6. 7. 8. 9. 10. 11. 12. 13. 14.	CATHODE CATHODE CATHODE CATHODE CATHODE ANODE	4. 5. 6. 7. 8. 9. 10. 11. 12. 13. 14.	GATE P-CH COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT) SOURCE P-CH SOURCE P-CH COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT) GATE N-CH COMMON DRAIN (OUTPUT) GATE N-CH COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT)		
5. 6. 7. 8. 9. 10. 11. 12. 13.	DRAIN, #2 DRAIN, #3 DRAIN, #3 DRAIN, #4 DRAIN, #4 GATE, #4 GATE, #4 GATE, #3 SOURCE, #3 GOURCE, #3 GOURCE, #2 SOURCE, #2	4. 5. 6. 7. 8. 9. 10. 11. 12. 13.	CATHODE CATHODE CATHODE CATHODE CATHODE CATHODE ANODE	4. 5. 6. 7. 8. 9. 10. 11. 12. 13.	GATE P-CH COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT) SOURCE P-CH SOURCE P-CH COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT) CATE N-CH COMMON DRAIN (OUTPUT)		

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